



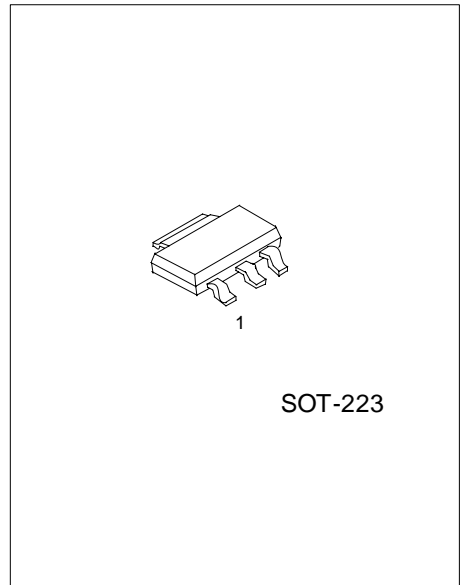
PZT4033

PNP SILICON TRANSISTOR

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DESCRIPTION

The UTC PZT4033 designed for high current general purpose amplifier applications.



*Pb-free plating product number:PZT4033L

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
PZT4033-AA3-R	PZT4033L-AA3-R	SOT-223	B	C	E	Tape Reel

<p>PZT4033L-AA3-R</p> <p>(1)Packing Type (2)Package Type (3)Lead Plating</p>	<p>(1) R: Tape Reel (2) AA3: SOT-223 (3) L: Lead Free Plating, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter-Base Voltage	V _{EBO}	-5	V
Power Dissipation	P _D	2	W
Collector Current	I _C	-1	A
Junction Temperature	T _J	-65 ~ +150	°C
Storage Temperature	T _{STG}	-65 ~ +150	

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

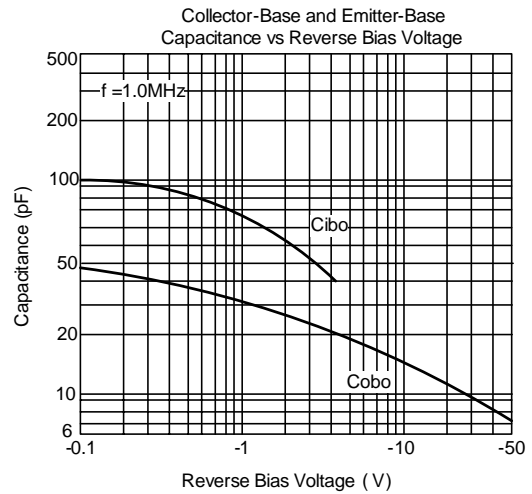
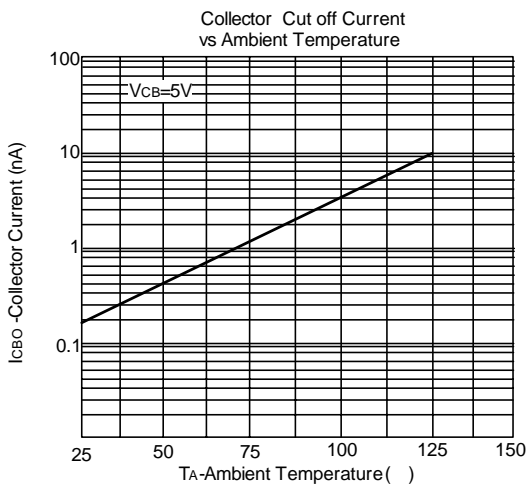
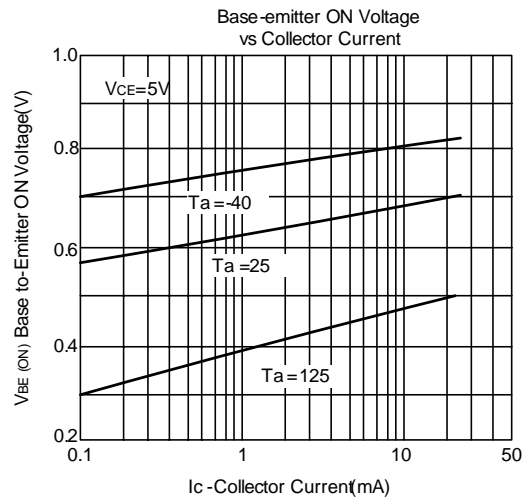
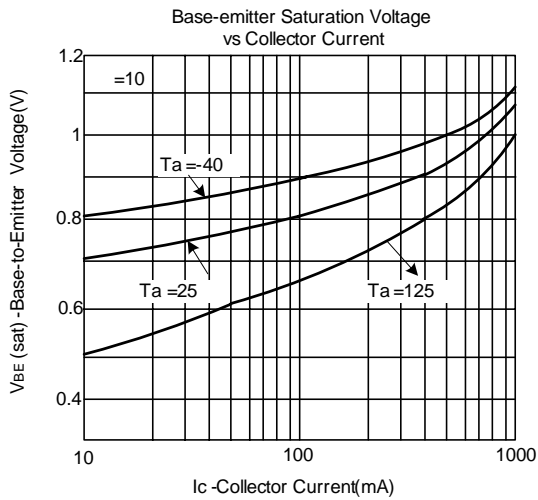
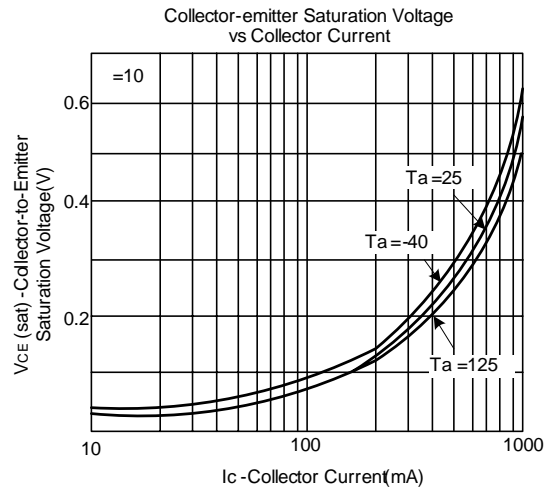
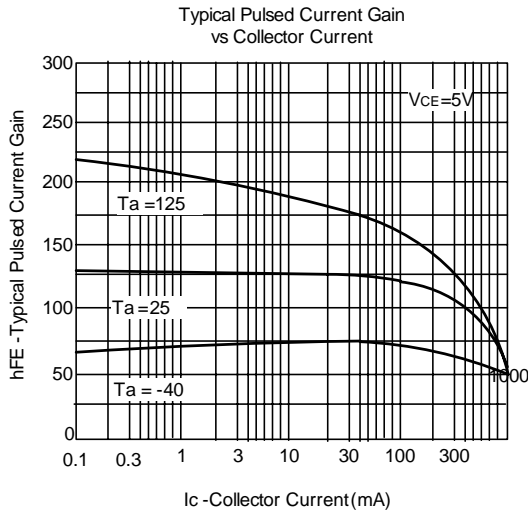
■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Thermal Resistance	θ _{JA}	62.5	°C/W

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-10μA, I _E =0	-80			V	
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-10mA, I _B =0	-80			V	
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-10μA, I _C =0	-5			V	
Collector Cut-off Current	I _{CBO}	V _{CB} =-60V, I _E =0			-50	nA	
Emitter Cut-off Current	I _{EBO}	V _{EB} =-5V, I _C =0			-10	nA	
DC Current Gain	h _{FE}	V _{CE} =-5V, I _C =-0.1mA	75		300		
		V _{CE} =-5V, I _C =-100mA	100				
		V _{CE} =-5V, I _C =-500mA	70				
		V _{CE} =-5V, I _C =-1A	25				
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-150mA, I _B =-15mA I _C =-500mA, I _B =-50mA			-0.15 -0.5	V	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-150mA, I _B =-15mA I _C =-500mA, I _B =-50mA			-0.9 -1.1	V	
Gain Bandwidth Product	f	V _{CE} = -10V, I _C = -50mA, f=1MHz	100			MHz	
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			20	pF	
Input Capacitance	C _{ib}	V _{EB} =-0.5V, I _C =0, f=1MHz			110	pF	
Switching Time	Turn-on Time	t _{ON}	I _C =-500 mA, V _{CE} = -30V, I _{B1} =- I _{B2} =-50mA			100	ns
	Storage Time	t _{STG}				350	ns
	Fall Time	t _F				50	ns

■ TYPICAL CHARACTERISTICS



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